



DOCUMENT CHANGE REQUEST

DCR number	757	Changes required for:	N/A	Originator:	Geraldine Chaumont
Date:	2013/03/04	Date sent:	2012/09/04	Organisation:	STMicroelectronics
Status:	IMPLEMENTED				

Title: Transistors Low Power RF NPN, based on type 2N3019

Number: 5201/011 Issue: 3

Other documents affected:

5201/019-5, 5202/014-5, 5203/010-4, 5204/002-4

Page:

5 and 14 or 15 or 17, depending on the specification number.

Paragraph:

1.4.1, 1.4.2 and 2.9 or 2.10 or 2.11, depending on the specification number.

Original wording:

No irradiation paragraph included in the detail specifications.

Proposed wording:

Insertion of a radiation level + total dose radiation chapter, as done in DCR707 for other detail specifications.

Justification:

The customers are asking for radiation level on bipolar transistors.

Attachments:

dcr757_attachment_rev1.docx, null

Modifications:

as per attachment

Approval signature:

Date signed:

2013-03-04